

Fast thermal and multi-physics simulation using model reduction and Sub-models for Electronics

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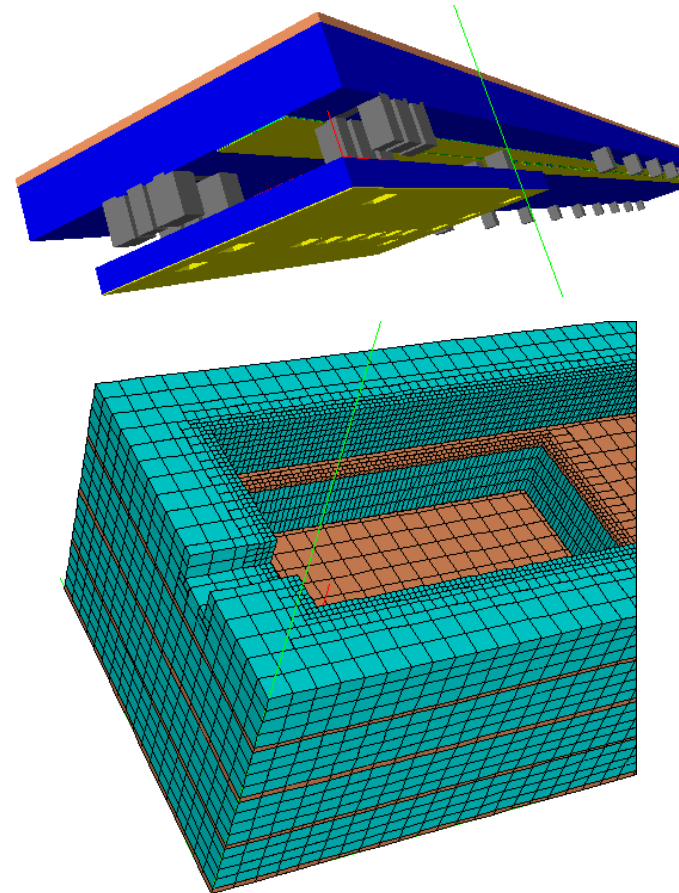
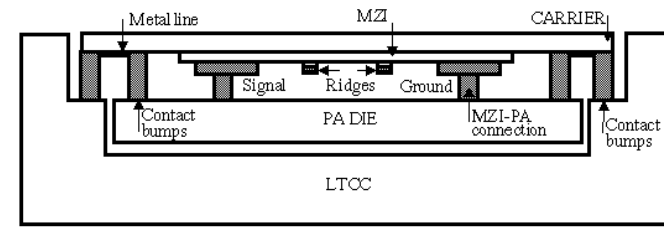
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Outline

- **Motivation and background**
- **State of the Project.**
- **Introduction to thermal simulations using multi-dimensional model reduction**
- **Applications of sub-models and model reduction**
- **Future Work**

Complicated thermal/multi-physics design problems

- **High power and non-uniformities** ($P \uparrow$, $f \uparrow$, chip size \downarrow , functionality \uparrow)
- **Development of new packaging/module technologies**
- **Multi-scale** — dev \rightarrow chip \rightarrow board \rightarrow ...
- **Reduction of production cycle-time and reliability.**
- **Reliability issues** — appropriate thermal management
- **Multi-physics** — thermal/EM/optical/mechanical coupling.



Current state of the project

● **Fast Thermal Modeling**

- **Developed sub-modeling techniques to allow for use of thermal library parts and enable fast simulation.**
- **Incorporated parameterized model reduction to create small BCI models for fast SS, transient simulation and compact models.**
- **Confirmed speed-ups of 100+ and accuracy of better than 1%.**

● **EM/optical simulation**

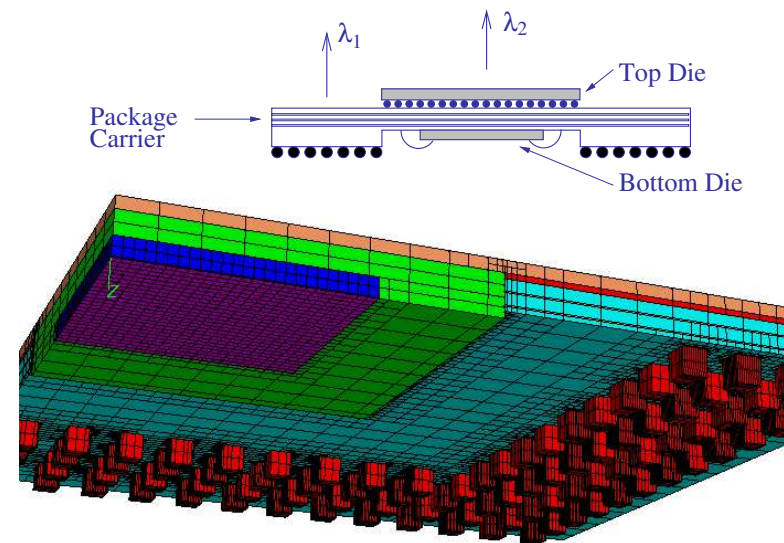
- **Fullwave integrated EM – based on TLM**
- **Simplified models base on thermal/electrical/optical interactions.**

● **Mechanical modeling**

- **Integrated FEM based stress/strain solver**
- **Developing the use of model reduction for stress/strain analysis.**

Simulation tools required for system and module design.

- Analytical — Simple geometries and boundary conditions.
- Fully detailed numerical simulations:
 - Become very large (200,000+ blocks) and computationally intensive.
 - Limited by model complexity.
 - Coupled physics simulation possible but time consuming. Bottleneck is often the need for a multi-scale thermal simulation.



Simulation tools Simplified or Compact models

- **Types**

- **Spreading resistances and multi-layer models.**
- **Optimized resistor networks – delphi.**
- **Matrix methods – model reduction**

- **Boundary condition Independence?**

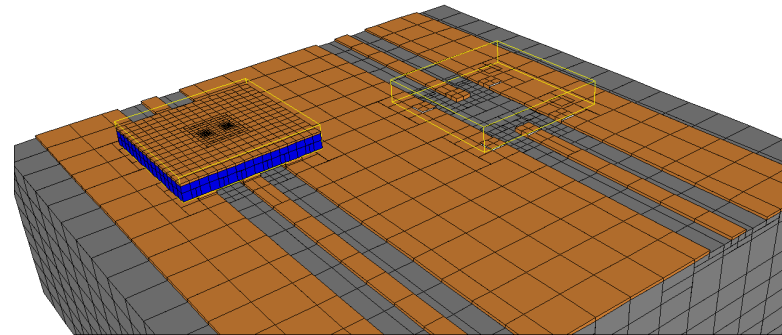
- **Limited to a small set of junction temperatures?**

- **Limited accuracy, flexibility and predictive capability.**

- **Questions arise for multiple power sources, transient and multiple points of interest.**

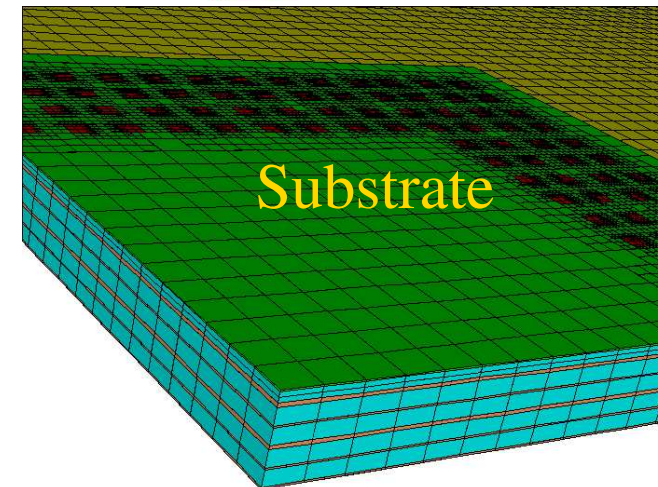
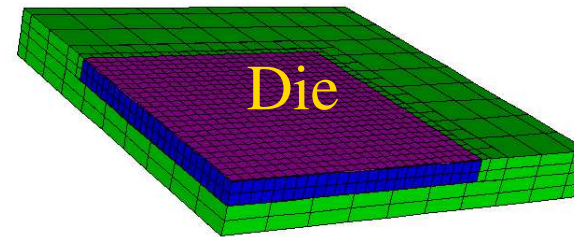
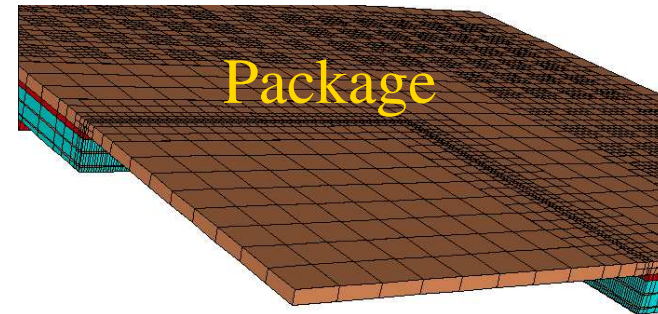
Quick thermal numerical solutions of full models

- Use a **Finite Difference numerical tool we have developed — Atar.**
 - Unstructured meshing
 - Multi-scale – device to board
 - Builds from geometry and a technology description
 - Extendable: Electro/optic/thermal coupling and Mechanical/thermal modeling.
- How to solve the problem of building and solving very large models?
 - Break the model in to pieces (which we call sub-models).
 - ▷ *Each piece is attached using a simple equation*
 - ▷ *All temperatures are determined*
 - Mathematically reduce the problem size using model reduction.

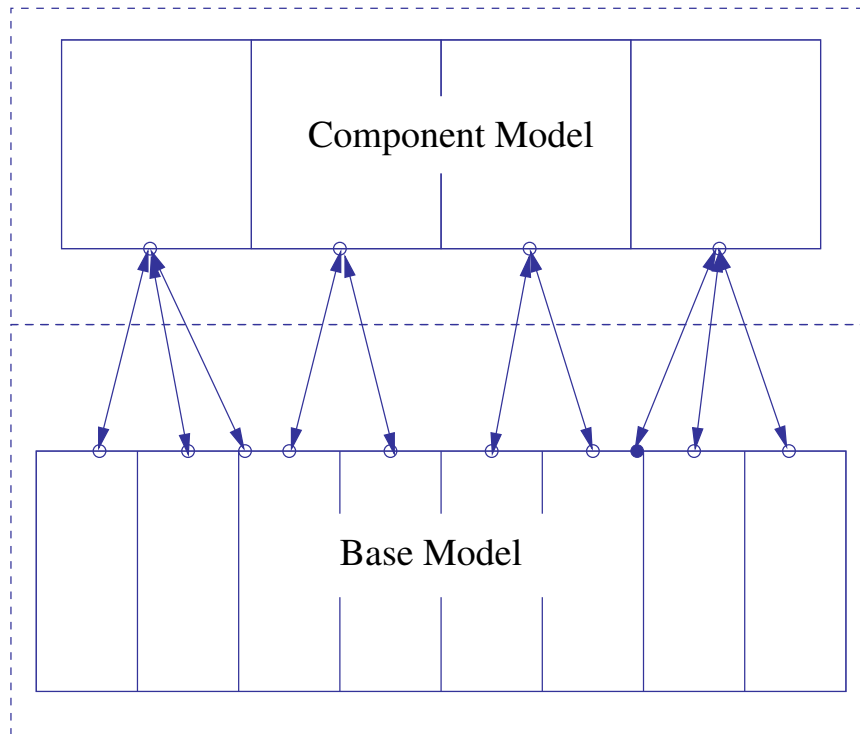


Sub-models: breaking the model up.

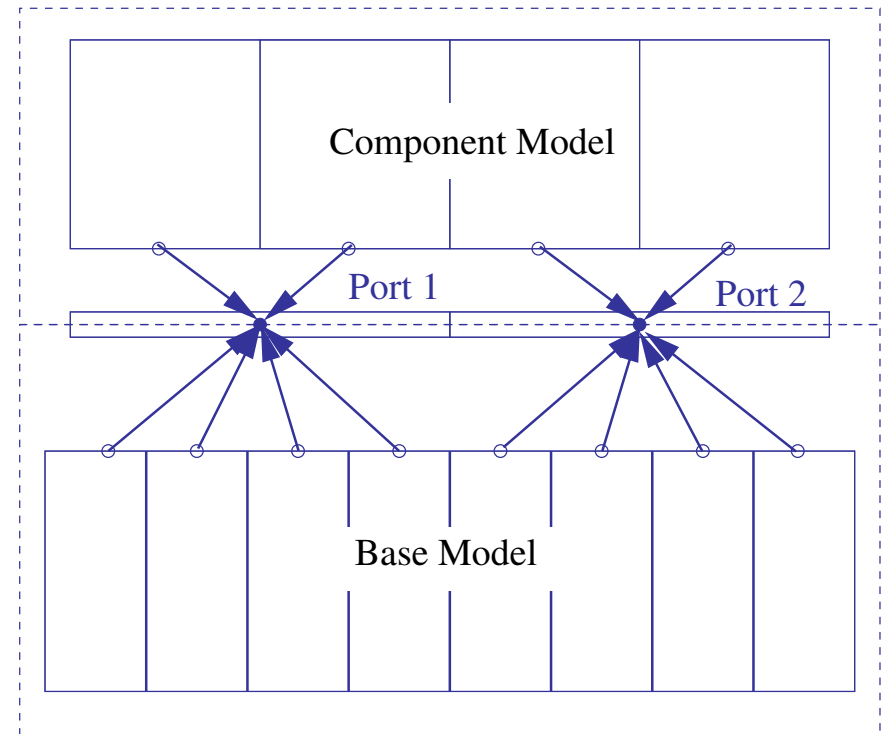
- **Break large detailed model into sub-models (well defined pieces)**
 - Connected by thermal ports which exchange heat.
 - Represented by a simple mathematical equation.
 - Complete response of component is captured
 - Can have “external” boundary conditions applied – usually as heat flow represented by external resistance.
- **Solve a “mixed model” of detailed base and connected sub-models.**
- **All internal temperatures of sub-model are available.**



Creation and application of sub-models



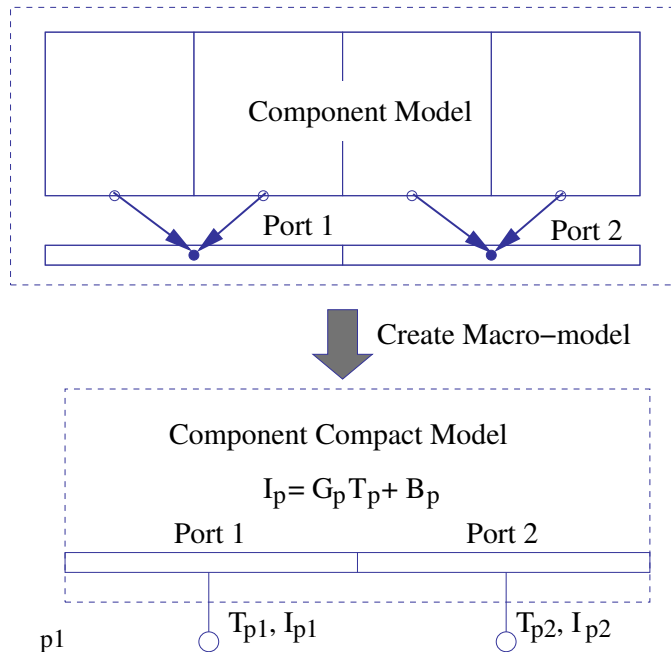
Fully detailed Model



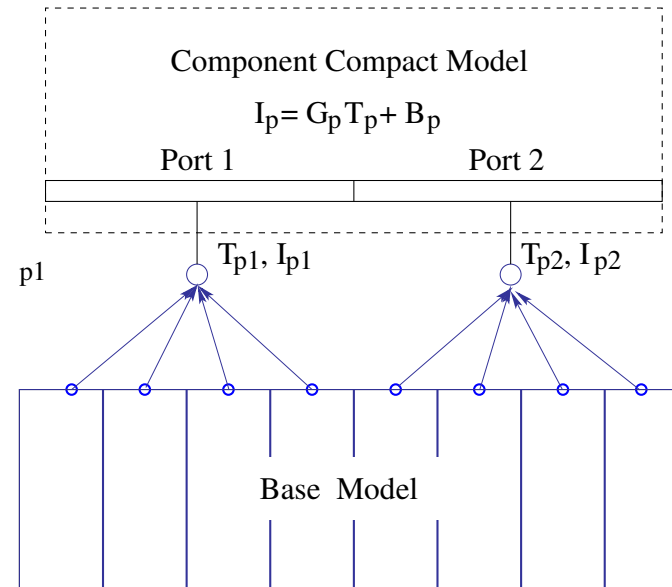
Definition of Ports

- **Separate model into pieces (base and sub-model).**
- **Define linking surface nodes to exchange heat.**
- **Define port surfaces between the two models.**
- **If port/block then an exact solution.**

Creation and application of sub-models



Create Sub-model



Link sub-model to base

- Create mathematical form of sub-model in terms of port temperatures (T_p) and currents (I_P).
- Connect sub-model to base using “attachment equation” .
- Solve “Mixed Model” for base model temperatures and port temperatures.
- Use port temperatures to obtain internal temperatures of sub-model.

Direct Generation of Sub-Model

- **The discretized form of the the thermal equation for the sub-model:**

$$G_S \mathbf{T} = B_S + M_p \mathbf{T}_p \quad (1)$$

$$\mathbf{I}_p = M_p^T \mathbf{T} \quad (2)$$

$$G_S(\lambda) = G + \sum_i^n \lambda_i G_{\lambda_i}$$

$$B_S(\lambda, T_m, T_f, P) = B + \sum_1^n \lambda_i T_{m_i} B_{\lambda_i} + \sum_1^m T_{f_k} B_{f_k} + \sum_1^p P_j B_{p_j}$$

- **Conductance matrix G – from discretization of detailed model.**
- **External boundary conditions are explicit — λ, T_m, T_f**
- **Internal powers are parameters — P**
- **Ports are defined using matrix M_p**
- **BCs are mapped using matrices B_f, B_λ and B_p .**

Direct Generation of Sub-Model

- Port currents can be defined as:

$$\mathbf{I}_p = \mathbf{M}_p^T \mathbf{G}_T^{-1} \mathbf{B}_T + \mathbf{M}_p^T \mathbf{G}_T^{-1} \mathbf{M}_p \mathbf{T}_p \quad (3)$$

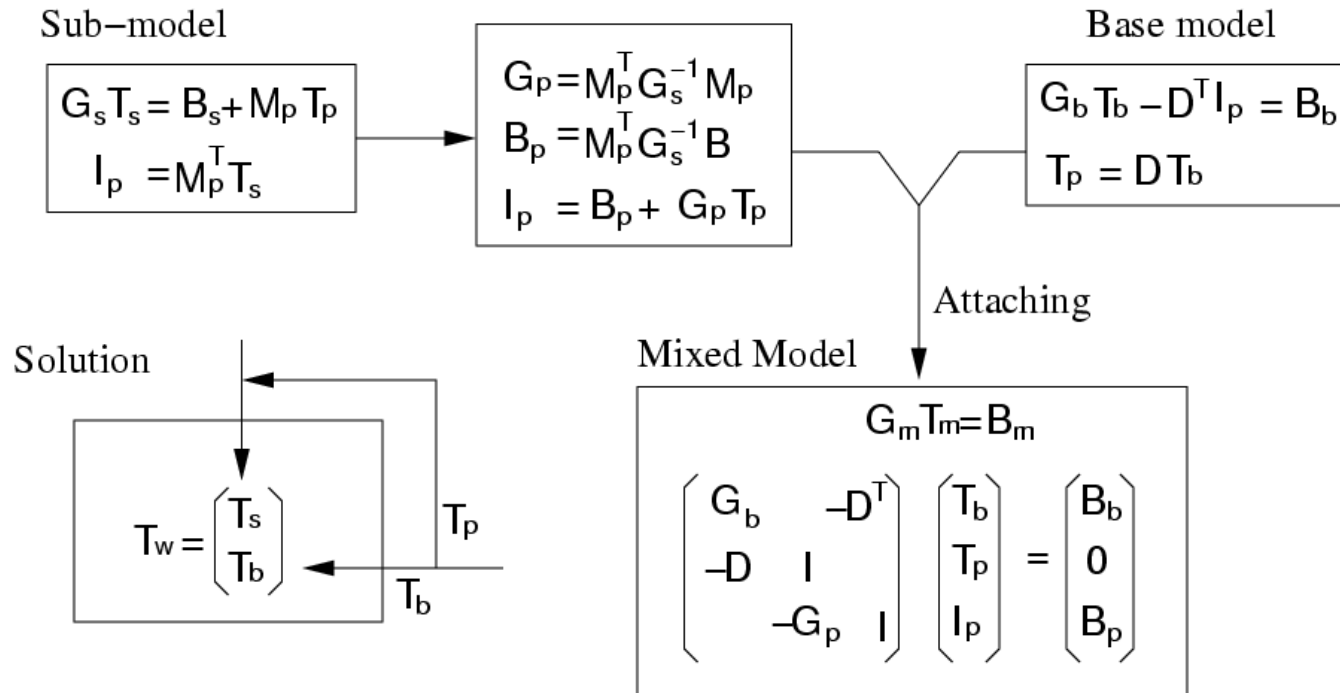
$$\mathbf{G}_p = \mathbf{M}_p^T \mathbf{G}_T^{-1} \mathbf{M}_p; \quad (4)$$

$$\mathbf{B}_p = \mathbf{M}_p^T \mathbf{G}_T^{-1} \mathbf{B}_T \quad (5)$$

$$\mathbf{I}_p = \mathbf{B}_p + \mathbf{G}_p \mathbf{T}_p \quad (6)$$

- This is the “attachment equation”- it is small ($n_p \times n_p$).
- We call this a “direct sub-model” as it is generated directly from the detailed model equations for the sub-model.

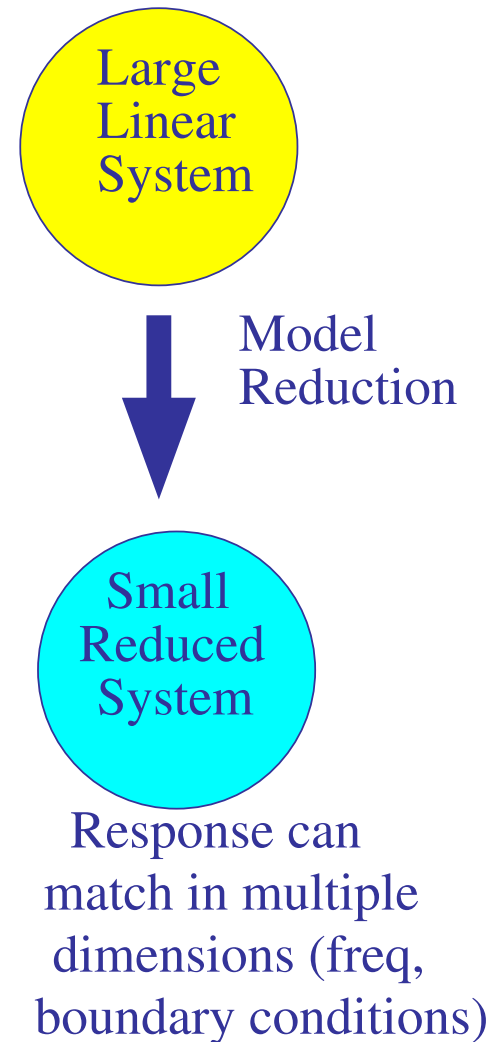
Solution of a mixed model with direct sub-models



- Can simulate a large complex model by breaking to pieces.
- Speed-up simulation and reduce memory requirements
- Create hierarchical sub-models
- However, each specification for a BC set of G_p and B_p requires a new LU decomposition of G_s . *Not Boundary condition independent!*

Model Reduction: making the problem smaller

- **Replace a large system of linear equations with a much smaller but equivalent one.**
- **Solution or creation of a sub-model can be performed in the reduced solution space.**
- **Very fast and accurate.**
- **The use of Multi-Dimensional Model Reduction allows us to include the boundary conditions applied to the model.**
- **Essentially making the reduced models boundary condition independent.**



Using Model Reduction

- A large (sparse) system replaced by a small (dense) system.
- Congruent transformation (T is mapped to \hat{T})
- Uses QR decomposition to form a multi-dimensional sub-space where:

$$T = Q\hat{T} \quad (7)$$

- Reduced network equation (much smaller size):

$$\left(\hat{G}_S + \sum_{i=1}^n \lambda_i \hat{G}_{h_i}\right) \hat{T} = \hat{B}_S + \sum_{i=1}^n \lambda_i T_m \hat{B}_{h_i} + \sum_{k=1}^m T_{f_k} \hat{B}_{f_k} + \sum_{j=1}^p P_j \hat{B}_{p_j} + \hat{M}_p T \quad (8)$$

- Boundary conditions are still explicit.

Reduced Sub-model creation

Internal temperatures:

The attachment equation:

$$\mathbf{I}_p = \mathbf{B}_p + \mathbf{G}_p \mathbf{T}_p$$

$$\hat{\mathbf{T}} = \hat{\mathbf{G}}_S^{-1} (\hat{\mathbf{B}}_S + \hat{\mathbf{M}}_p \mathbf{T}_p)$$

$$T_S = \mathbf{Q} \hat{\mathbf{T}}$$

$$\mathbf{G}_p = \hat{\mathbf{M}}_p^T \hat{\mathbf{G}}_S^{-1} \hat{\mathbf{M}}_p$$

$$\mathbf{B}_p = \hat{\mathbf{M}}_p^T \hat{\mathbf{G}}_S^{-1} \hat{\mathbf{B}}_T$$

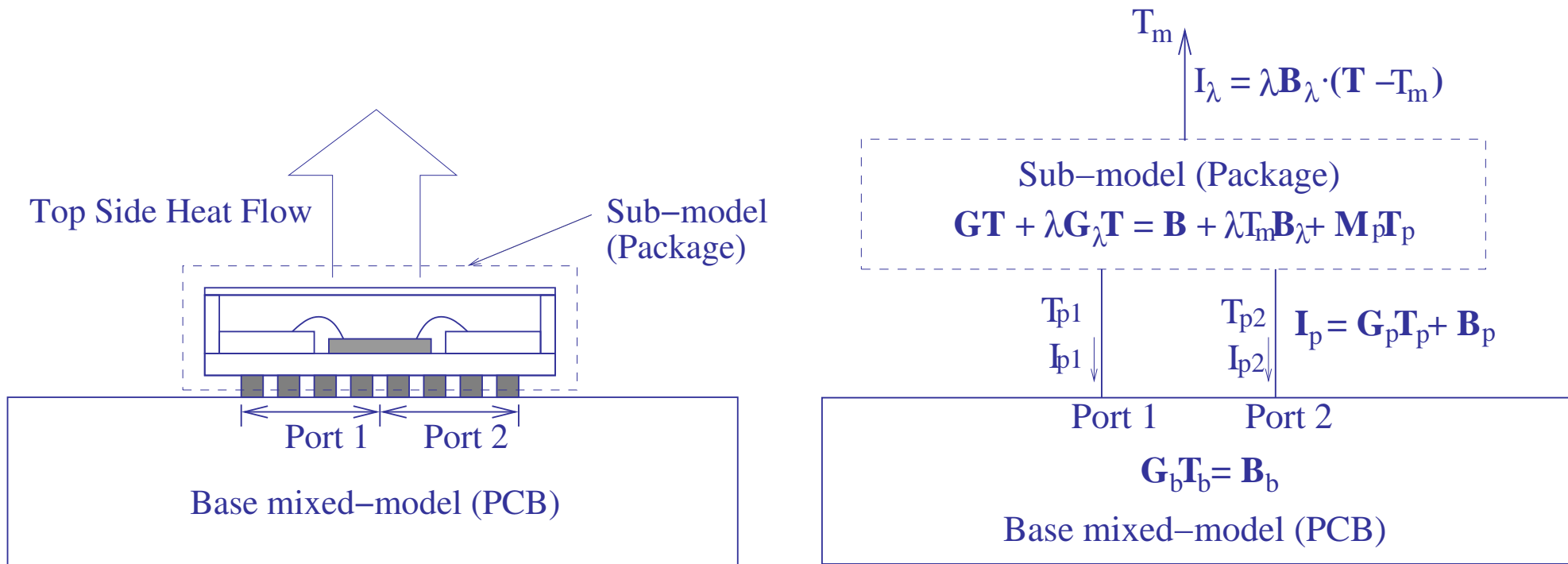
Junction temperatures

$$\mathbf{T}_{jct} = \mathbf{S} \mathbf{Q} \hat{\mathbf{T}}$$

$$I_{\lambda_i} = \lambda_i B_{\lambda_i} \cdot (\mathbf{Q} \hat{\mathbf{T}} - T_{m_i})$$

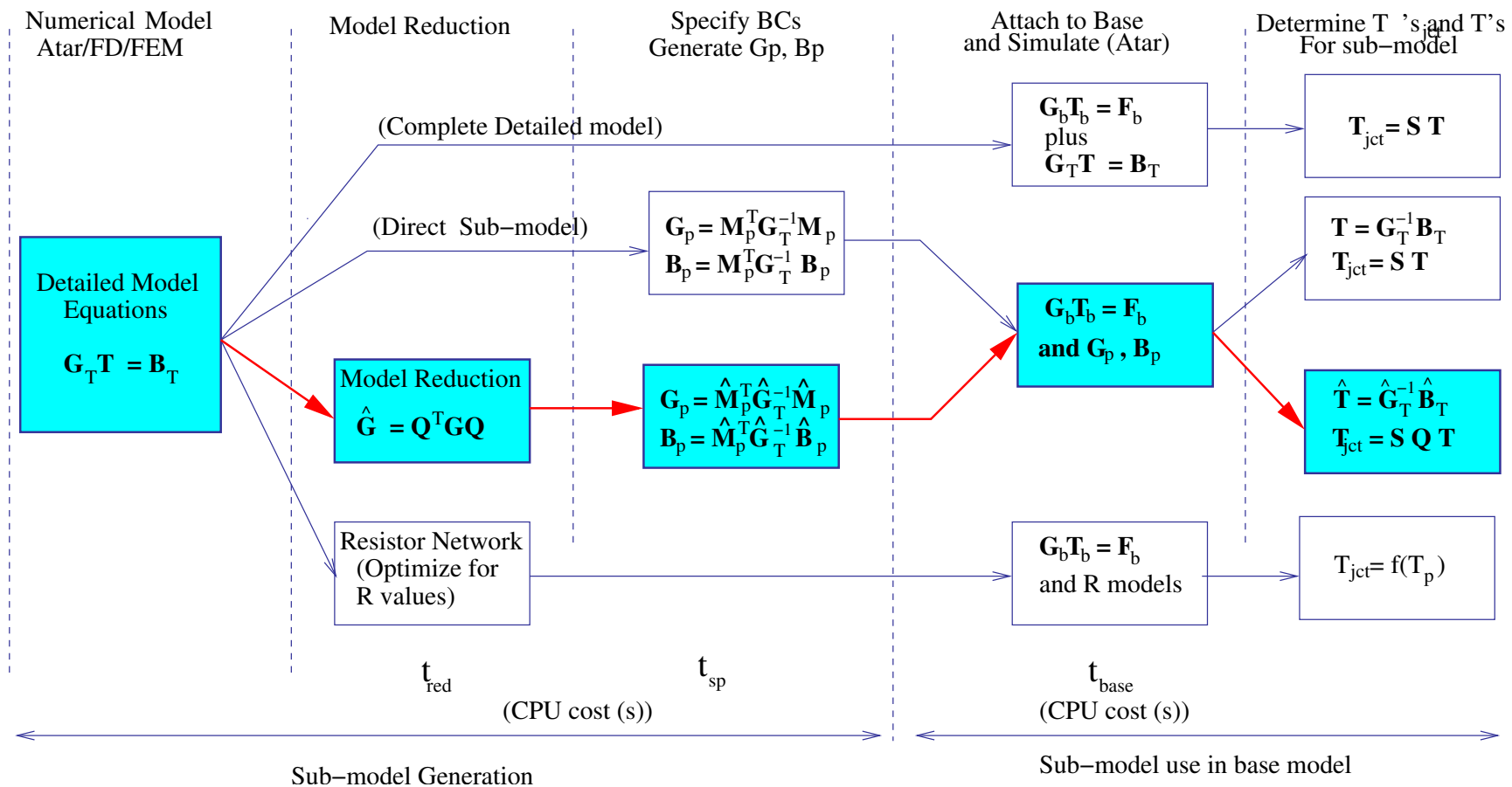
- As $\hat{\mathbf{G}}_S$ is much smaller than \mathbf{G}_S we can form \mathbf{G}_p and \mathbf{B}_p in less than a second prior to simulation of the mixed model.
- Model reduction does introduce some error

Reduced Sub-model Summary



- **Characterize submodel using — T_p and I_p .**
- **External boundary conditions parameterized.**
- **Use Model reduction so we can generate G_p and B_p very quickly (less than a second)**

Overview of Simulation algorithms

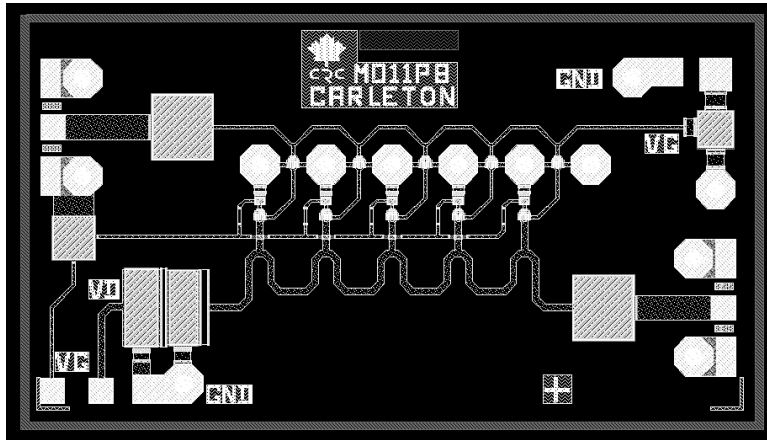


- **Comparison of four simulation schemes.**
- **Use of MDMR and submodels is quick and supplies all temperatures.**

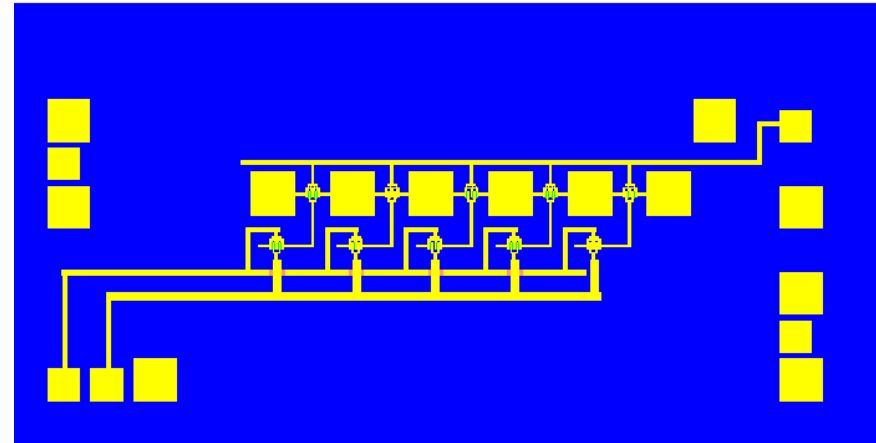
Summary of Atar, MR and Sub-modeling

- **Sub-modeling allows us to solve big models on “normal” computers**
- **Model Reduction allows us to build BC parametrized models.**
 - **One LU (SS solution) to do MR for BCI model.**
 - **Size reduction from 100,000s to 10’s of nodes.**
 - **FAST!**
 - **All internal temperatures!**
- **New attachment procedure – constant heat flow ports.**
- **Verification**
 - **Compared both transient and SS models with analytical solutions for simple problems (<1% error).**
 - **Compared both transient and SS models with “fully detailed” numerical models (Atar and commercial solvers) (<1**
 - **Math works!**
 - **Input is correct (Geo, power, material properties) output is correct (T(t)).**

Example: Power Amplifier for optical modulator



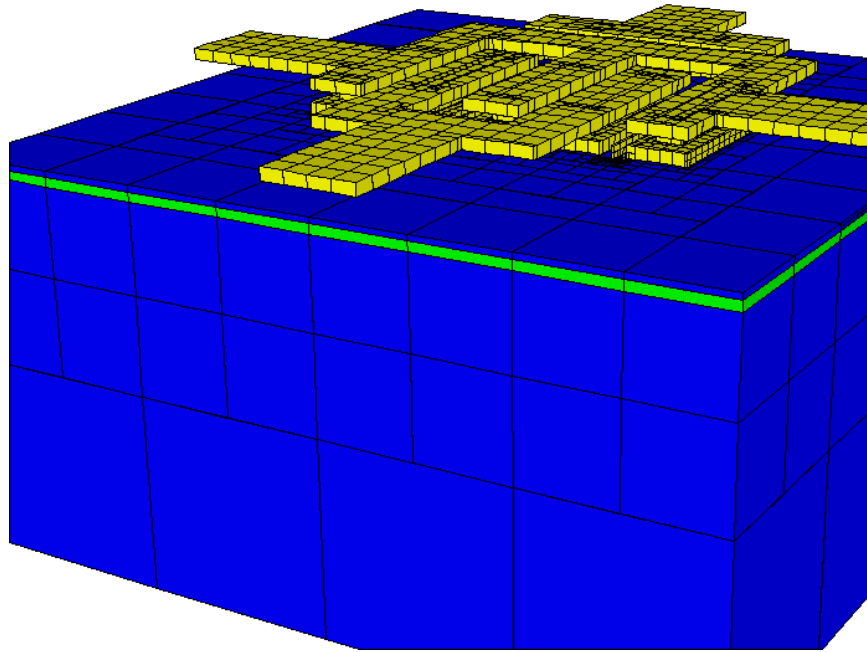
Photograph of Die



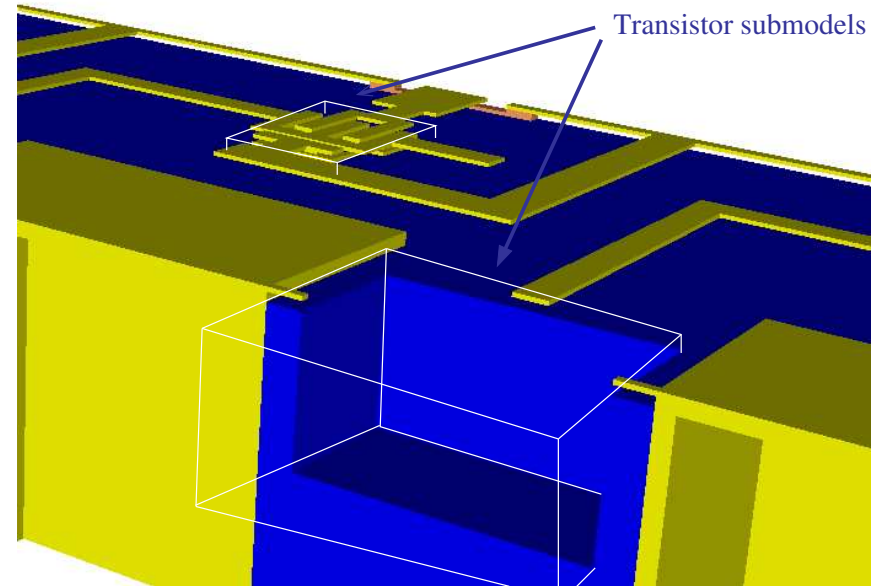
Astar model of complete PA

- **5-section cascode gain PA**
- **10 multi-finger GaAs FET transistor power cells**
- **Fine meshing of pinch-off region.**
- **Detailed description of backend metalization**
- **Fully detailed model is very large! (300,000 blocks)**

Sub-model transistor



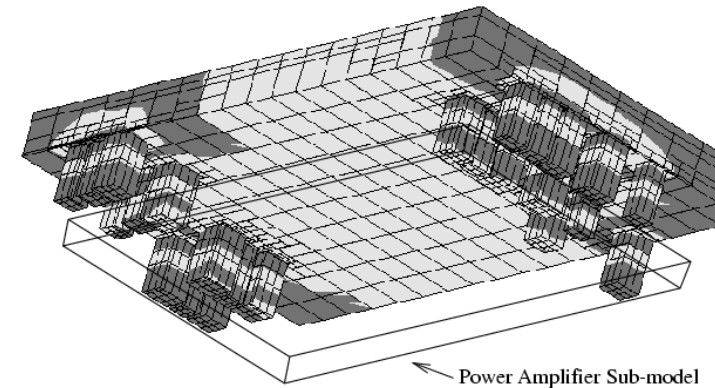
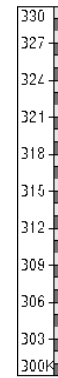
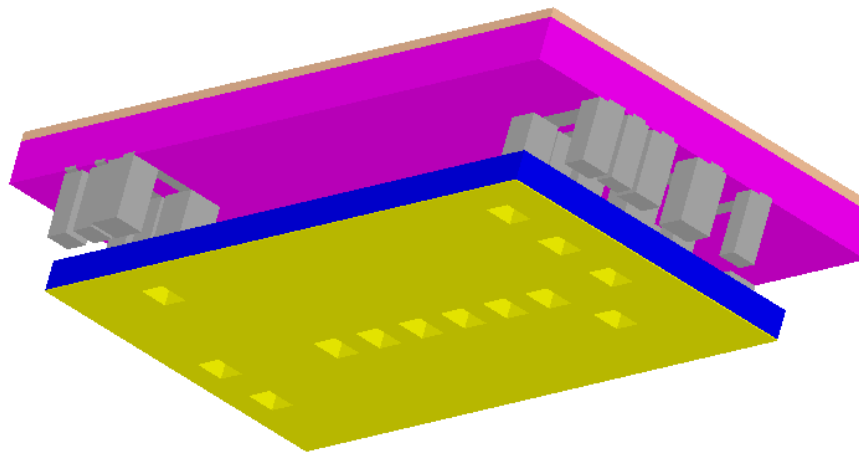
Transistor sub-model



Base Model

- **Build each four finger transistor cell as sub-model**
- **Use 9 ports – one for each side and the metal connections.**
- **Base uses 10 transistor cells sub-models.**

Hierarchical Submodels — Power amplifier as a sub-model

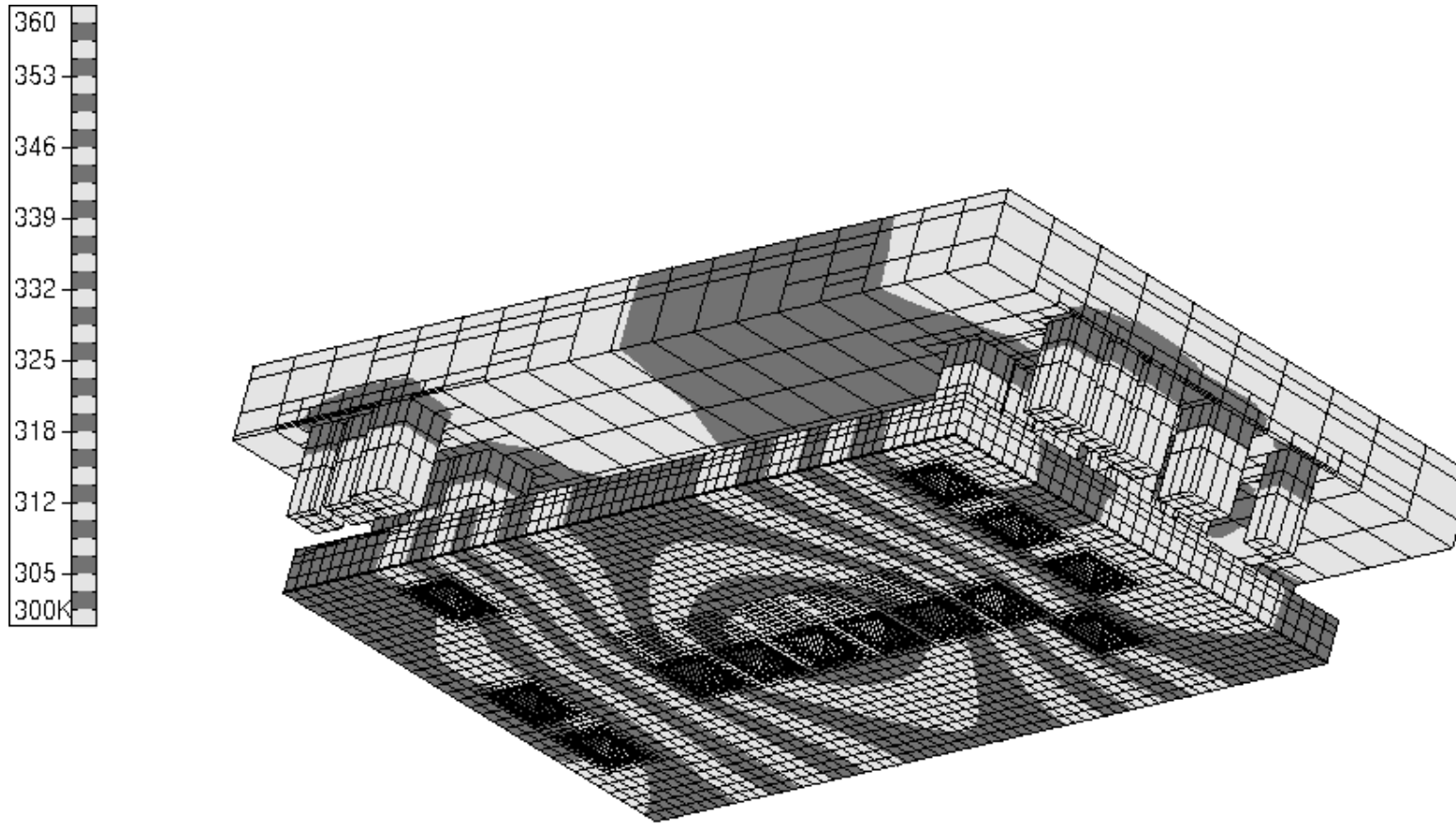


Detailed model of PA and InP Carrier

Base after solution

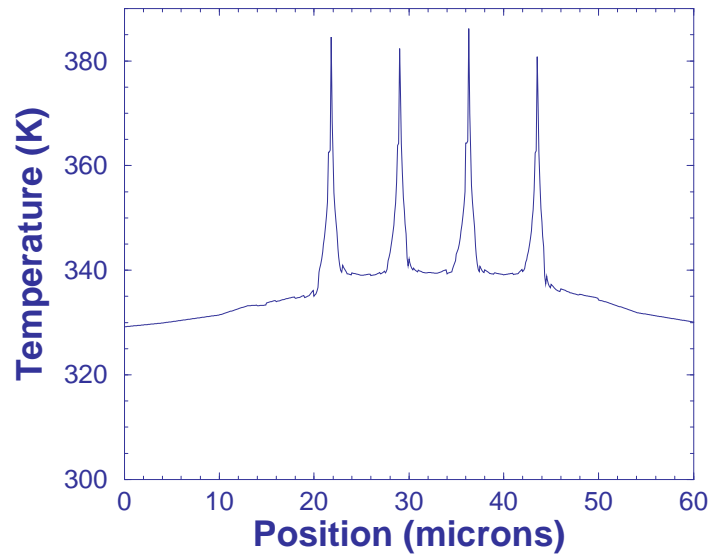
- Build PA as a 12-port sub-model containing 10 transistor submodels
- Solve InP mixed-model with attached PA submodel.
- Calculate PA temperatures from port temperatures of the InP mixed model.
- Calculate transistor temperatures from port temperatures of the PA mixed-model.

Temperature contours



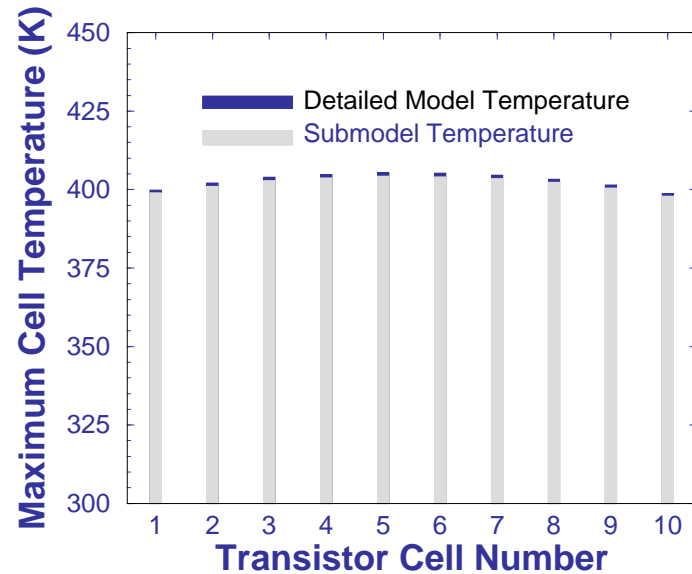
- **Obtain all internal temperatures.**
- **PA sub-model contains heat flow parameter for backside flow.**

Internal Temperatures



Finger temperatures

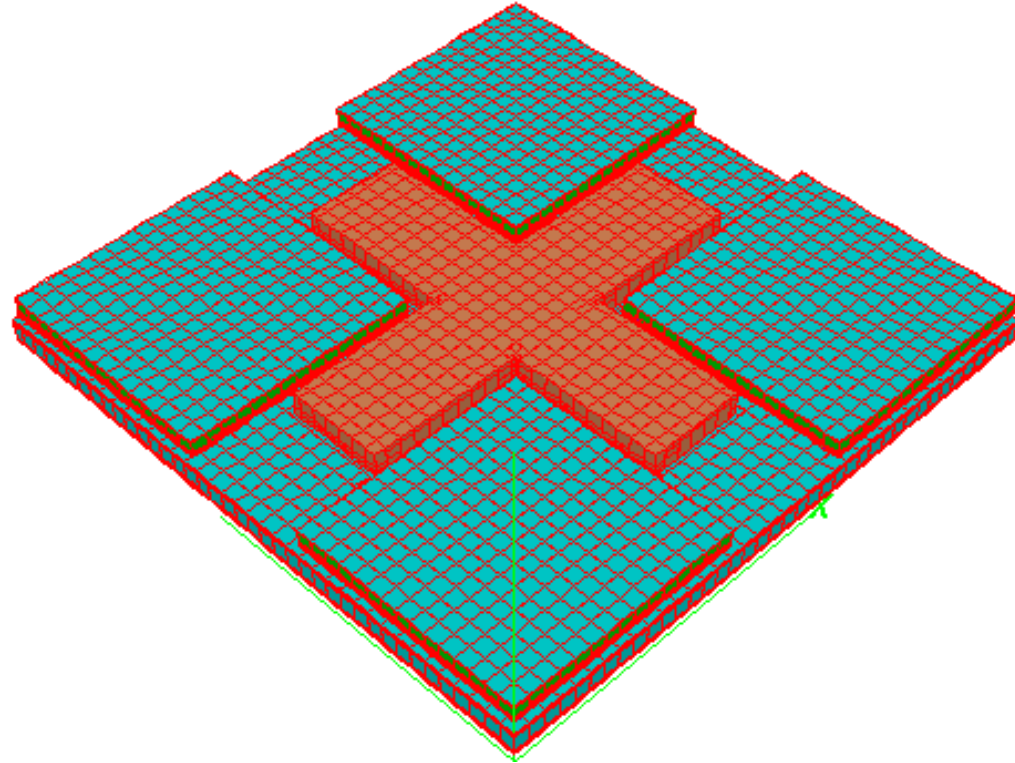
- Compare to “fully detailed” numerical model of all components.
- Accurate to better than 2%.



Junction Temperatures

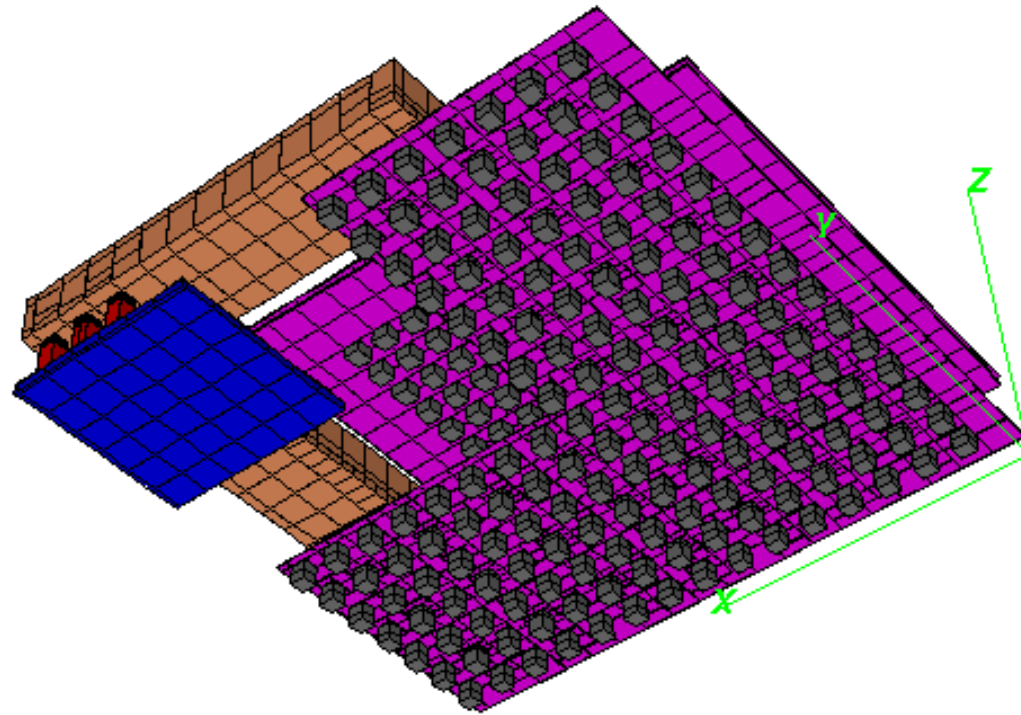
Example: ATI Technologies 216T9NFBGA13FH Processor

- Working with DY4.
- Model based on Semiconductor Insights report.
 - PCB package substrate
 - ATI graphics chip
 - Four DDR SDRAM memory chips



ATI Technologies 216T9NFBGA13FH Processor

- **Include lots of internal detail**
- **Base model plus 4 submodels for Memory and 1 for die**
- **Built reduced model for connection to a board.**
- **Paramaterized heat flow off cross and memory chips.**



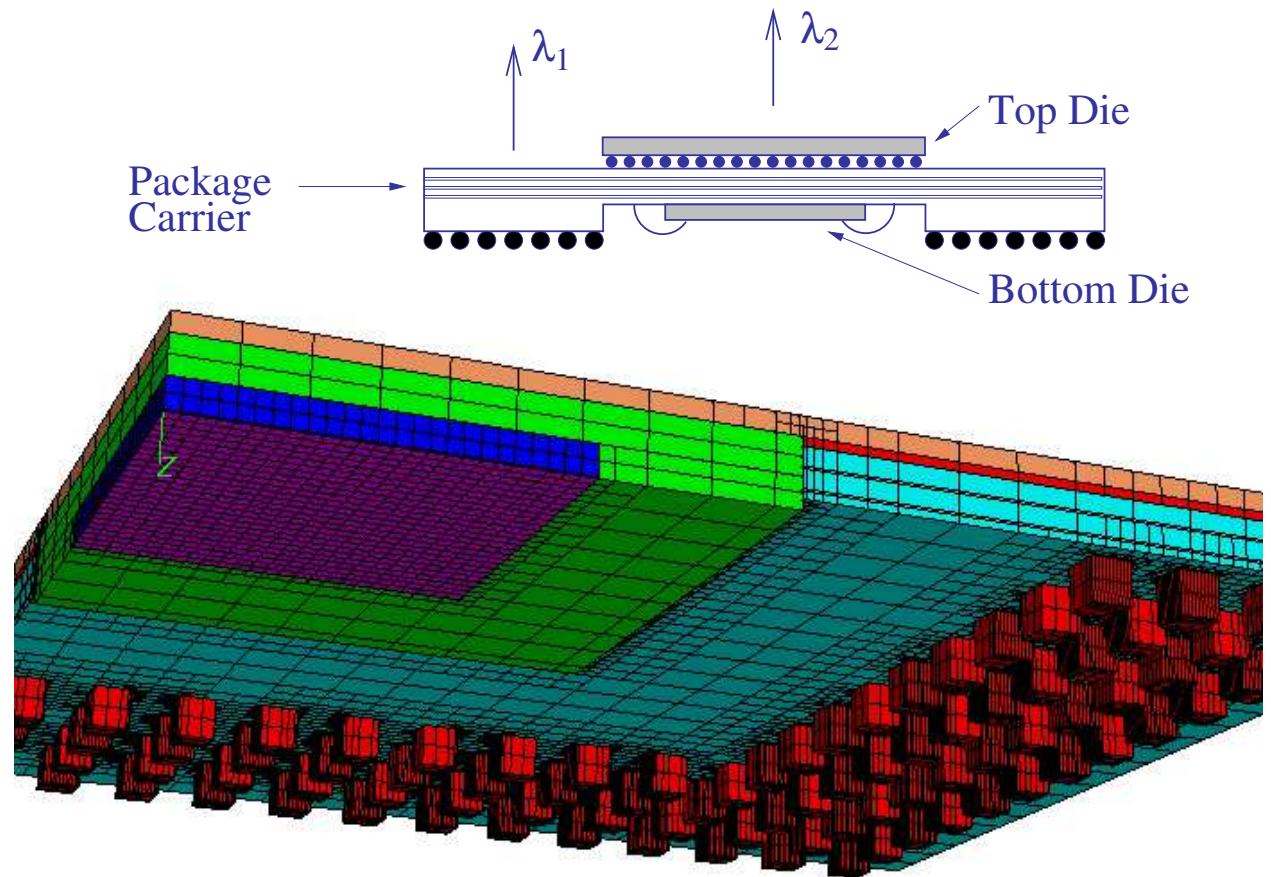
ATI Technologies 216T9NFBGA13FH Processor

- Preliminary results match reported θ_{JC} to within 5%.
- Future work will involve integration of module into cards.

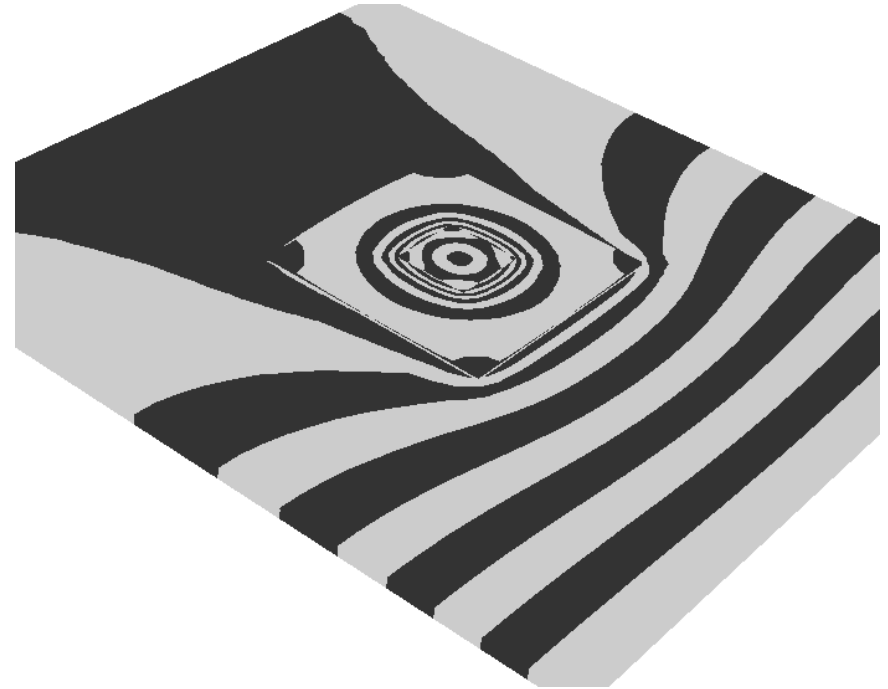
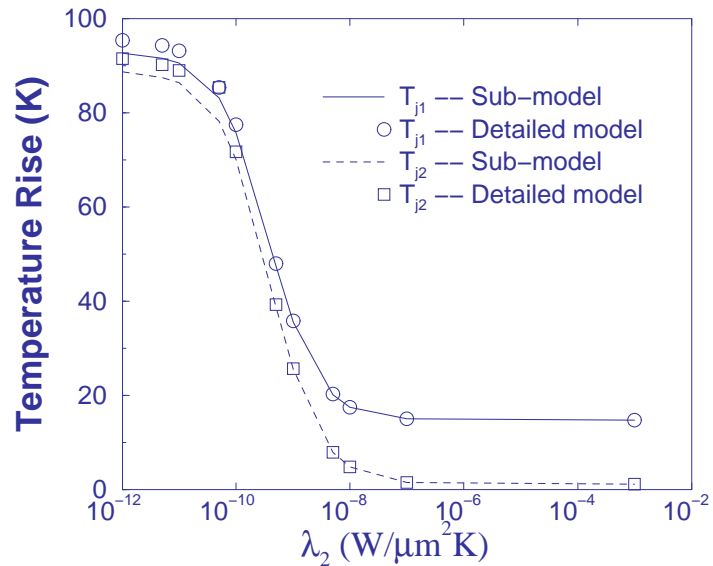


Second Example: MCMBGA

- Large pinout multichip package
- Need a boundary condition independant model
- Paramaterize heat flow off top and sides of package.



Attachment and boundary condition independance



Junction temperatures

Base and sub-model contours

- Used models with 4 to 64 ports.
- Varied heat flow off the top and sides.
- Model reduction error less than 1%
- Error is primarily due to port configuration not model reduction.

Model size and reduction time

Model	Detailed Size	Sub-model size		t_{red} (sec)
		Reduced	Attached	
PA				
Transistor	19,900	11×11	9×9	46
Die¹	63,943	60×60	12×12	233
MCMBGA				
Package	73,129	32×32	4×4	415

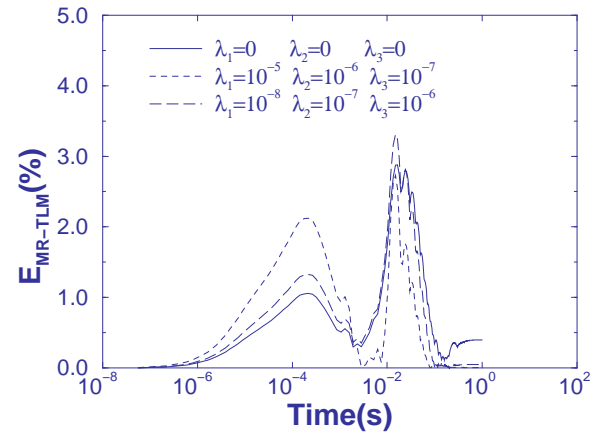
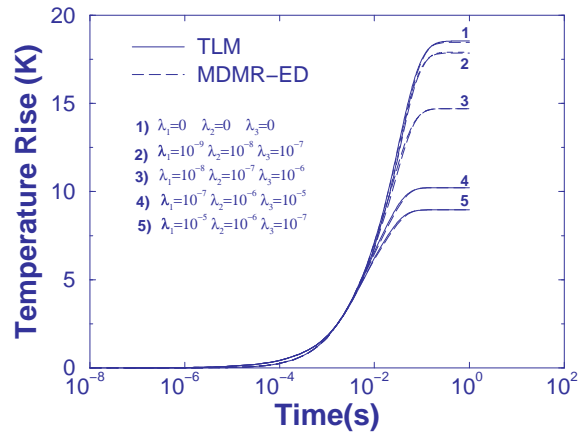
- **Model size and sub-model generation time for each component in PA and MCMBGA models**
- **Die model is formed out of a die substrate and 10 transistor sub-models**

Model size, speed-up and accuracy

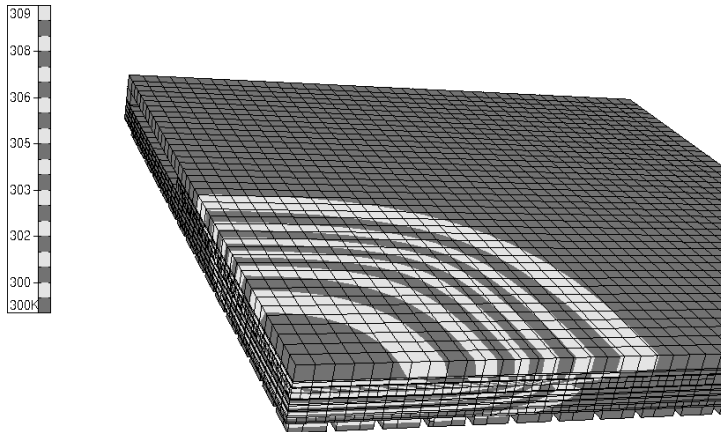
Model	Size	t_{sol} (sec)	T_j (K)
PA			
Detailed	269,547	768	105.4
InP+Die sub-model	1212	16	104.3
	Speed-up of 48		$\Delta T_j = 1.0\%$
MCMBGA			
Detailed	77,929	213	95.4
PCB+package sub-model	4804	2.20	93.1
	Speed-up of 97		$\Delta T_j = 2.5\%$

- **Solution time and junction temperature obtained from comparison of fully detailed solution of all components and a mixed-model using sub-models.**

CBGA: Transient Simulations

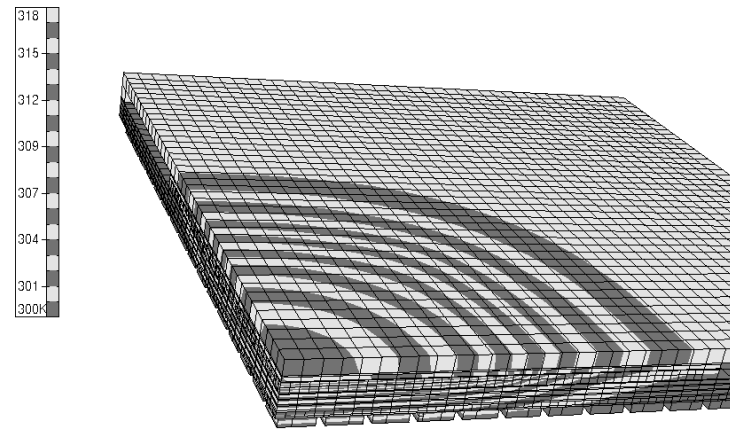


Temperatures



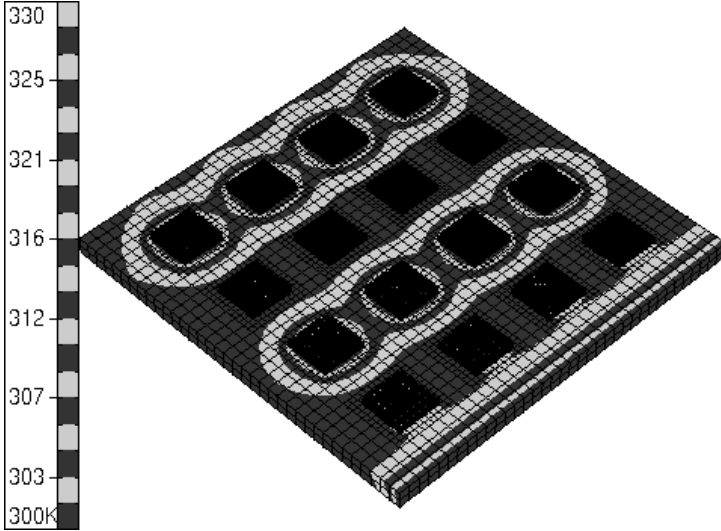
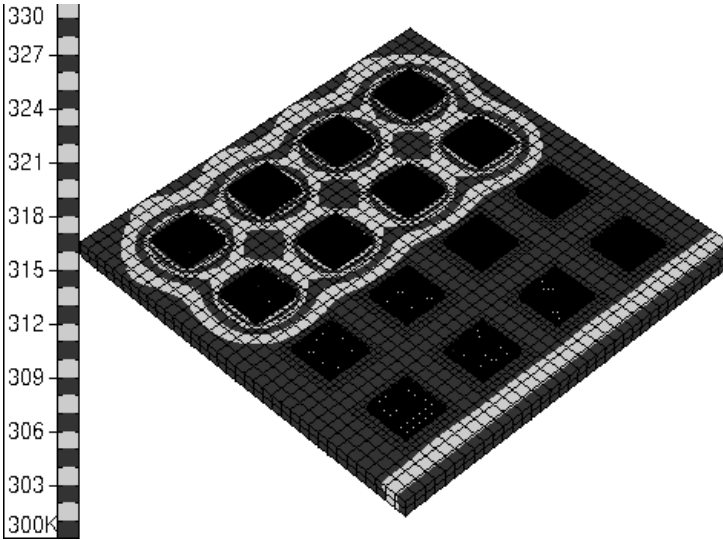
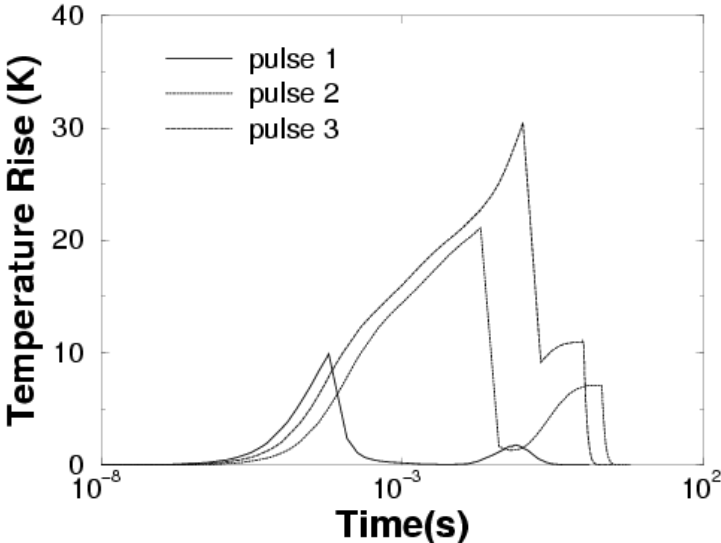
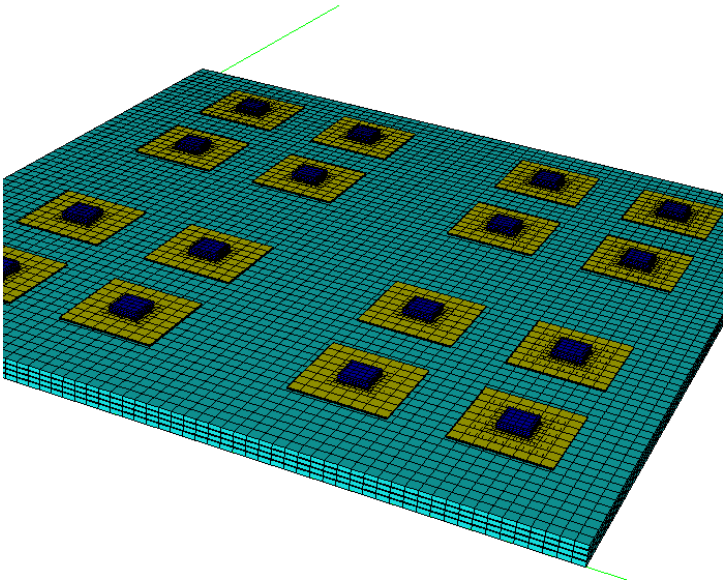
1/2 SS

Errors



SS

Submodel: Transient Simulations



Future Work

- **Full System Modeling**
 - **Steady-state and transient – hierarchical modeling, thermal libraries.**
 - **Convection models and boundaries.**
 - **Advanced technologies – heat pipes.**
- **Non-linear modeling (Convective BCs, $K(T)$)**
- **Multiphysics**
- **Application Work**
 - **Higher level of integration (3D, SOC, SIP) – Chip/Package co-design**
 - **Heat Removal (Optimization, Heat pipes, others?)**
- **Making the work accessible.**
 - **Web based application server.**
 - **GUI for Atar/MR based analysis**
 - **Industrial inspired projects.**